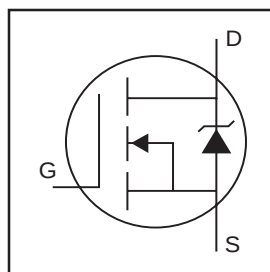


IRFBE30SPbF

IRFBE30LPbF

HEXFET® Power MOSFET

- Dynamic dv/dt Rating
- Repetitive Avalanche Rated
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Lead-Free



$$V_{DS} = 800V$$

$$R_{DS(on)} = 3.0\Omega$$

$$I_D = 4.1A$$

Description

Third Generation HEXFETs from International Rectifier provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.



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IRFBE30S



TO-262
IRFBE30L

Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ $T_C = 25^\circ C$	Continuous Drain Current, V_{GS} @ 10V	4.1	A
I_D @ $T_C = 100^\circ C$	Continuous Drain Current, V_{GS} @ 10V	2.6	
I_{DM}	Pulsed Drain Current ①	16	
P_D @ $T_C = 25^\circ C$	Maximum Power Dissipation	125	W
	Linear Derating Factor	1.0	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy (Thermally Limited) ②	260	mJ
I_{AR}	Avalanche Current ①	4.1	A
E_{AR}	Repetitive Avalanche Energy ①	13	mJ
dv/dt	Peak Diode Recovery dv/dt ③	2.0	V/ns
T_J	Operating Junction and	-55 to + 150	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

Thermal Resistance

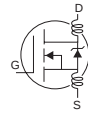
	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	1.0	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	—	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient	—	—	62	

IRFBE30S/LPbF

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Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	800	—	—	V	$V_{GS} = 0\text{V}$, $I_D = 250\mu\text{A}$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.90	—	$V/^\circ\text{C}$	Reference to 25°C , $I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	3.0	Ω	$V_{GS} = 10\text{V}$, $I_D = 2.5\text{A}$ ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$
g_{fs}	Forward Transconductance	2.5	—	—	S	$V_{DS} = 100\text{V}$, $I_D = 2.5\text{A}$
I_{DSS}	Drain-to-Source Leakage Current	—	—	100	μA	$V_{DS} = 800\text{V}$, $V_{GS} = 0\text{V}$
		—	—	500		$V_{DS} = 640\text{V}$, $V_{GS} = 0\text{V}$, $T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20\text{V}$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20\text{V}$
Q_g	Total Gate Charge	—	—	78	nC	$I_D = 4.1\text{A}$
Q_{gs}	Gate-to-Source Charge	—	—	9.6		$V_{DS} = 400\text{V}$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	45		$V_{GS} = 10\text{V}$, See Fig. 6 & 13 ④
$t_{d(on)}$	Turn-On Delay Time	—	12	—	ns	$V_{DD} = 400\text{V}$
t_r	Rise Time	—	33	—		$I_D = 4.1\text{A}$
$t_{d(off)}$	Turn-Off Delay Time	—	82	—		$R_G = 12\Omega$
t_f	Fall Time	—	30	—		$R_D = 95\Omega$, See Fig. 10 ④
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L_S	Internal Source Inductance	—	7.5	—		
C_{iss}	Input Capacitance	—	1300	—	pF	$V_{GS} = 0\text{V}$
C_{oss}	Output Capacitance	—	310	—		$V_{DS} = 25\text{V}$
C_{rss}	Reverse Transfer Capacitance	—	190	—		$f = 1.0\text{MHz}$, See Fig. 5

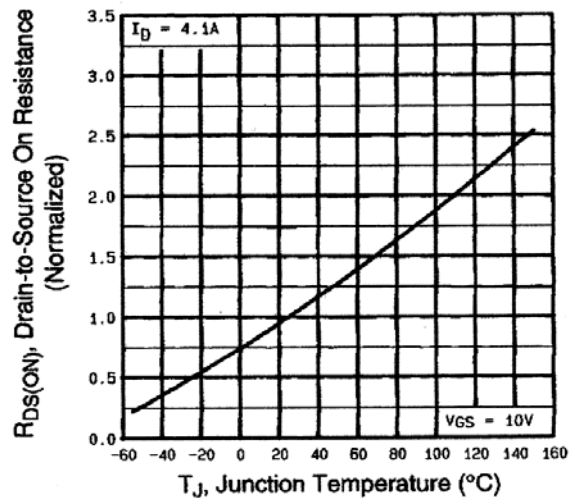
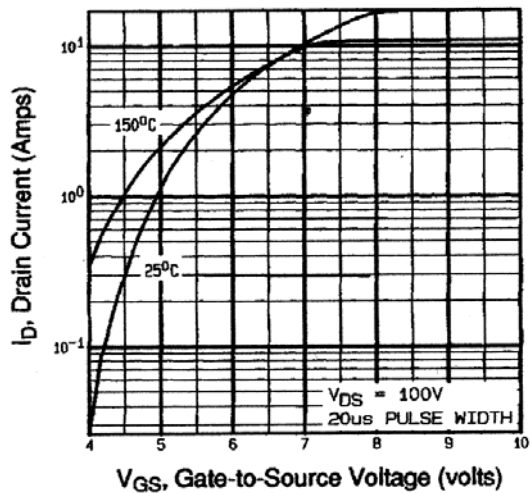
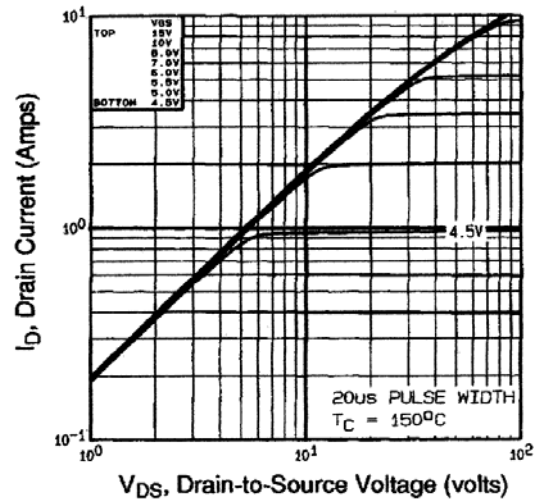
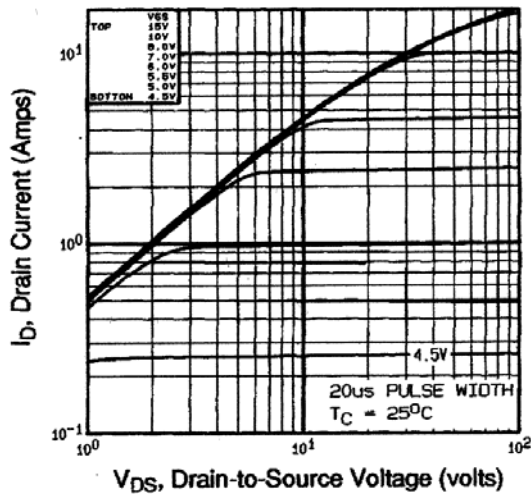


Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	4.1	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	16		
V_{SD}	Diode Forward Voltage	—	—	1.8	V	$T_J = 25^\circ\text{C}$, $I_S = 4.1\text{A}$, $V_{GS} = 0\text{V}$ ④
t_{rr}	Reverse Recovery Time	—	480	720	ns	$T_J = 25^\circ\text{C}$, $I_F = 4.1\text{A}$
Q_{rr}	Reverse Recovery Charge	—	1.8	2.7	nC	$di/dt = 100\text{A}/\mu\text{s}$ ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11).
- ② $V_{DD} = 50\text{V}$, starting $T_J = 25^\circ\text{C}$, $L = 29\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 4.1\text{A}$. (See Figure 12).
- ③ $I_{SD} \leq 4.1\text{A}$, $di/dt \leq 100\text{A}/\mu\text{s}$, $V_{DD} \leq 600$, $T_J \leq 150^\circ\text{C}$.
- ④ Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.



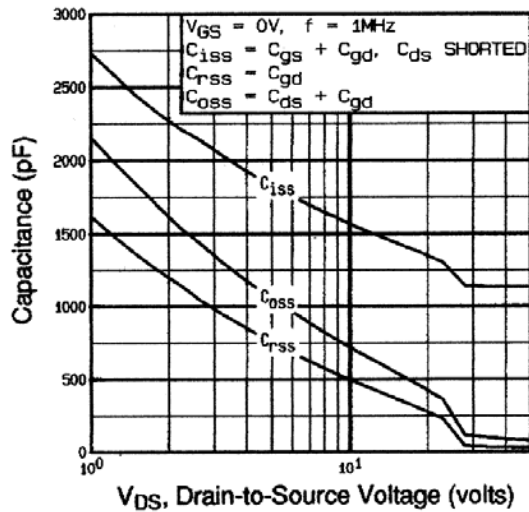


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

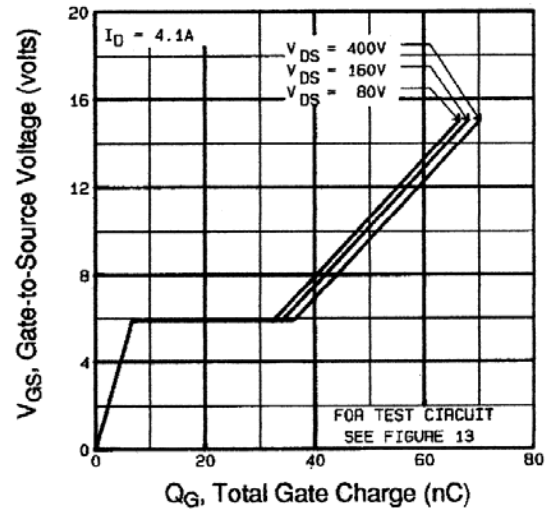


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

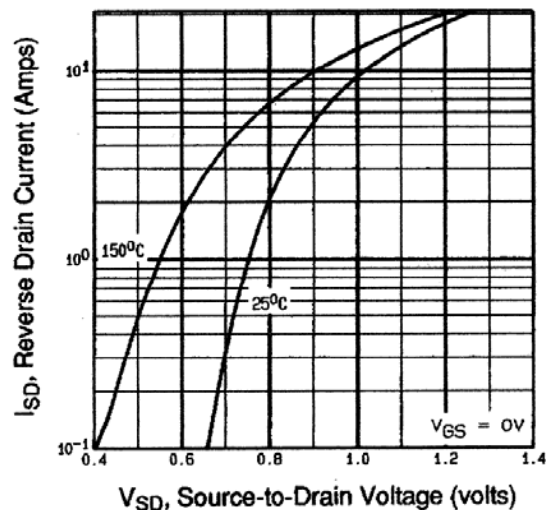


Fig 7. Typical Source-Drain Diode Forward Voltage

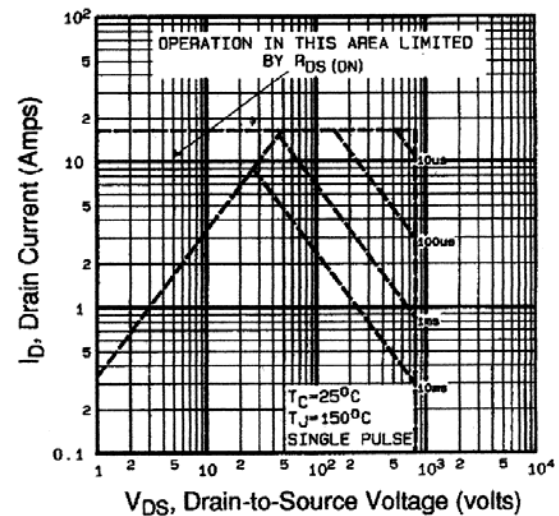


Fig 8. Maximum Safe Operating Area

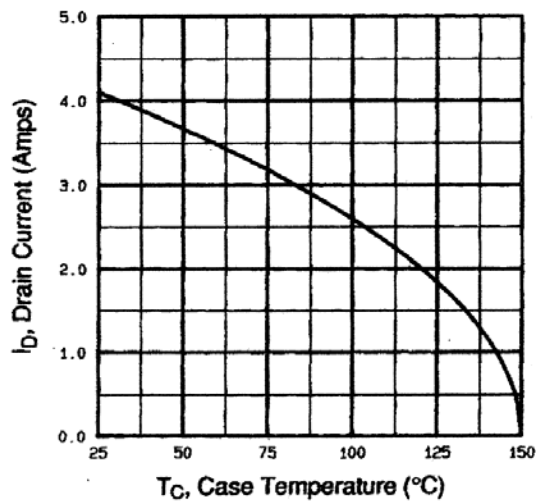


Fig 9. Maximum Drain Current Vs. Case Temperature

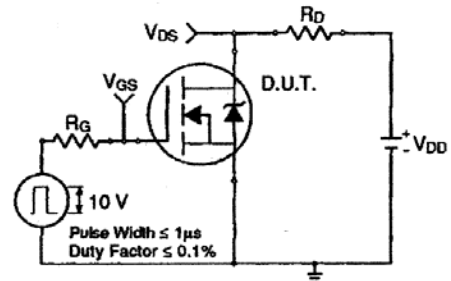


Fig 10a. Switching Time Test Circuit

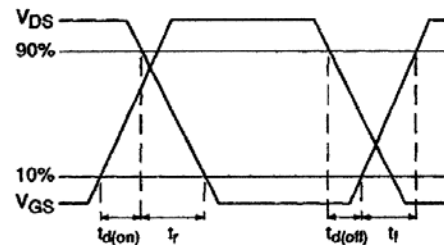


Fig 10b. Switching Time Waveforms

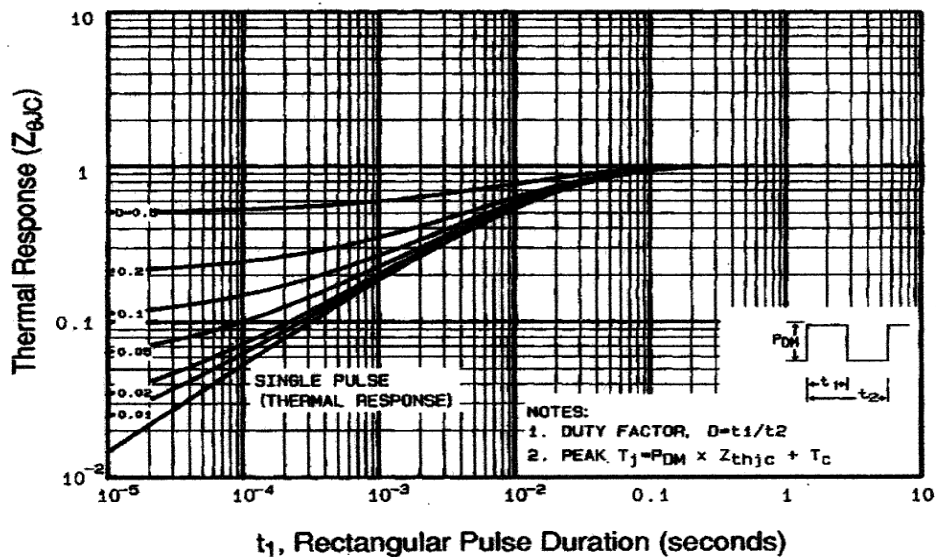


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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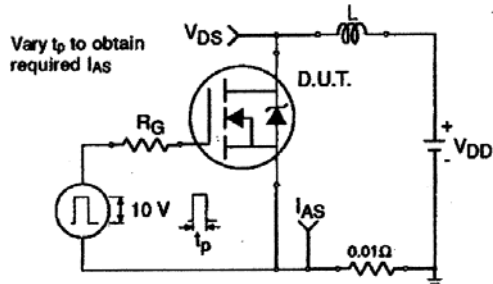


Fig 12a. Unclamped Inductive Test Circuit

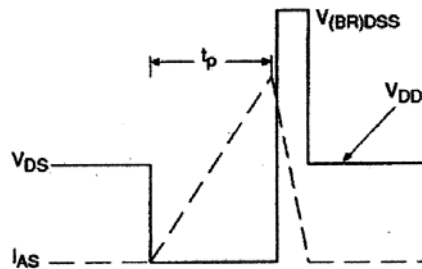


Fig 12b. Unclamped Inductive Waveforms

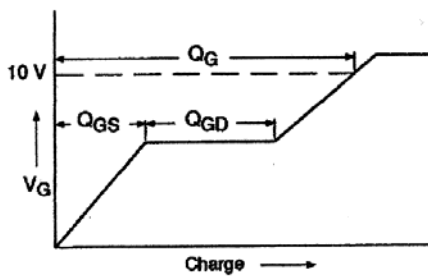


Fig 13a. Basic Gate Charge Waveform

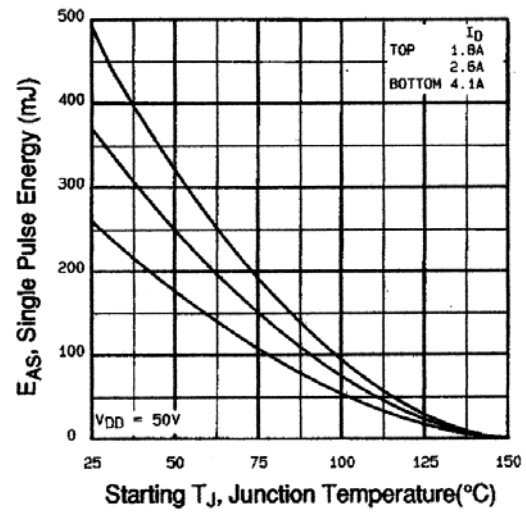


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

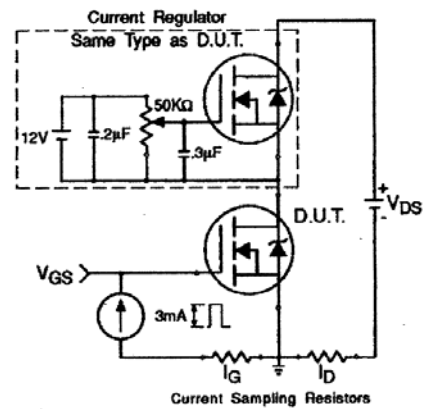
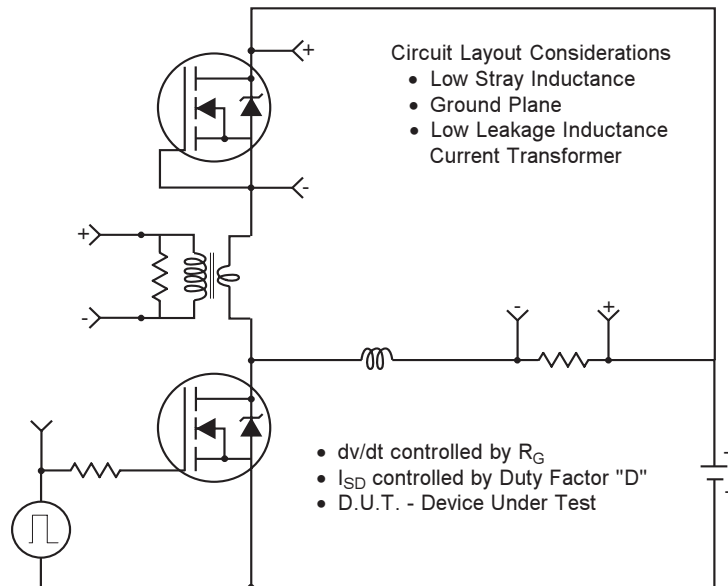


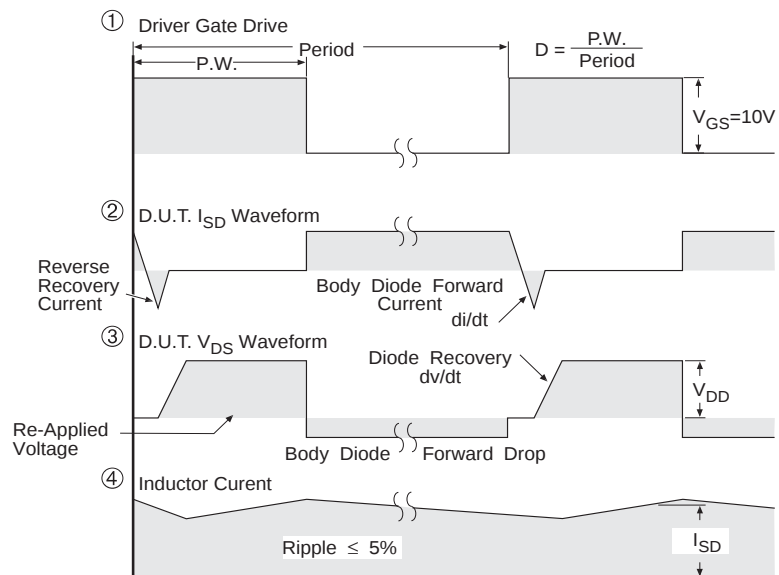
Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



* Reverse Polarity for P-Channel

** Use P-Channel Driver for P-Channel Measurements

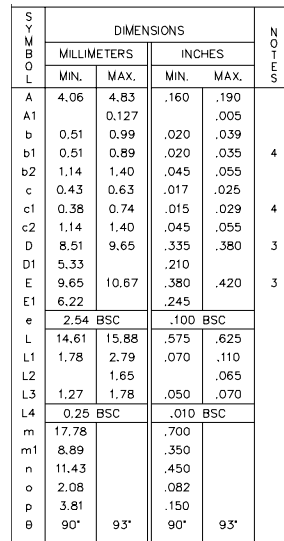


*** $V_{GS} = 5.0V$ for Logic Level and 3V Drive Devices

Fig-14 For N-Channel HEXFETS

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Dimensions are shown in millimeters (inches)



HEXFET	IGBTs, CoPACK	DIODES
1.- GATE	1.- GATE	1.- ANODE *
2.- DRAIN	2.- COLLECTOR	2.- CATHODE
3.- SOURCE	3.- EMITTER	3.- ANODE

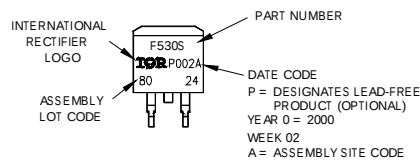
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES]
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH; MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.

 DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.

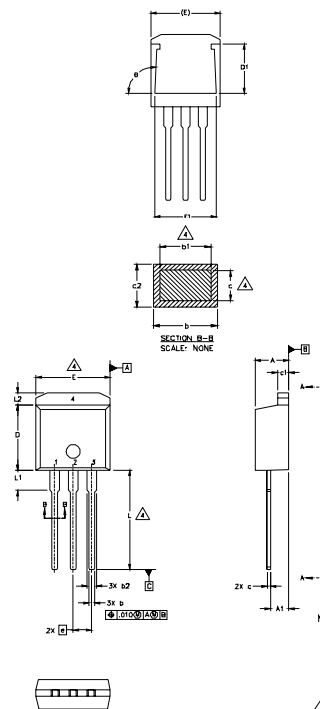
5. CONTROLLING DIMENSION: INCH.

OR



TO-262 Package Outline

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	4
A1	2.03	2.92	.080	.115	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	
b2	1.14	1.40	.045	.055	4
c	0.38	0.63	.015	.025	
c1	1.14	1.40	.045	.055	
c2	0.43	.063	.017	.029	3
D	8.51	9.65	.335	.380	
D1	5.33		.210		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	13.46	14.09	.530	.555	
L1	3.56	3.71	.140	.146	
L2		1.65		.065	

LEAD ASSIGNMENTS

HEXFET

- 1. - GATE
- 2. - DRAIN
- 3. - SOURCE
- 4. - DRAIN

IGBT

- 1 - GATE
- 2 - COLLECTOR
- 3 - EMITTER

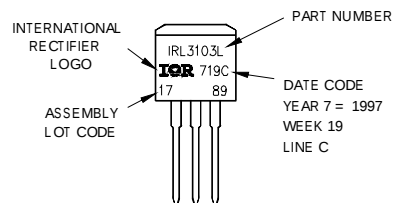
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4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY
5. CONTROLLING DIMENSION: INCH.

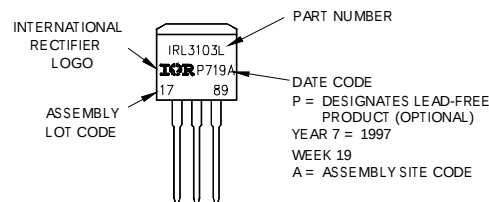
TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position indicates "Lead-Free"



OR

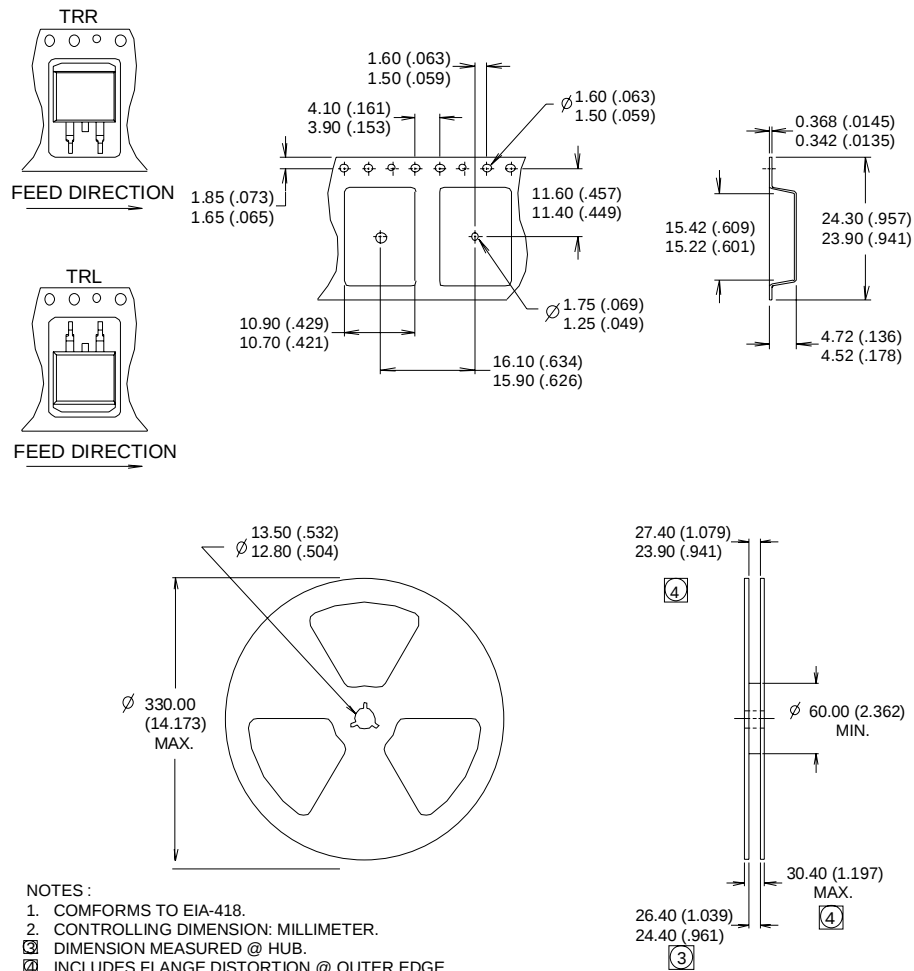


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D²Pak Tape & Reel Information

Dimensions are shown in millimeters (inches)



Data and specifications subject to change without notice.

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TAC Fax: (310) 252-7903

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